

Silicon Creations and Calibre

Ensuring Silicon Results will Match Circuit Simulation

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Extraction Products

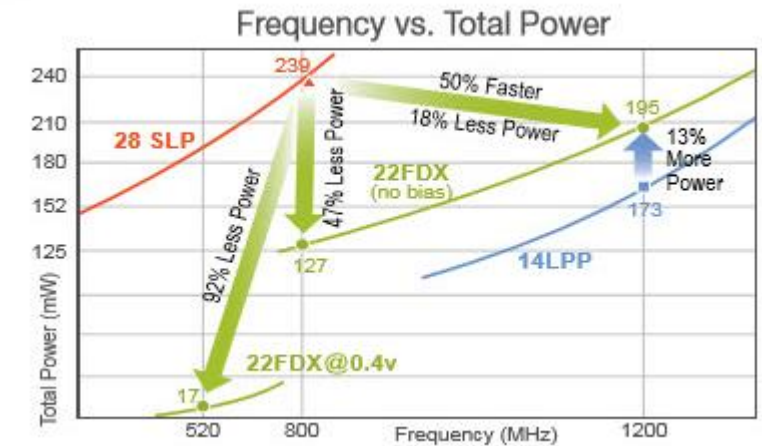
Agenda: Calibre xACT For Advanced Node Parasitic Extraction

- Advanced node challenges
- Field solver vs. table-based approaches to extraction
- Impact of errors
- Calibre xACT hybrid approach to extraction
- Results: accuracy
- Product portfolio and flows

Problem Statement: Accurate Silicon Prediction

Efficient calculation and integration of circuit components

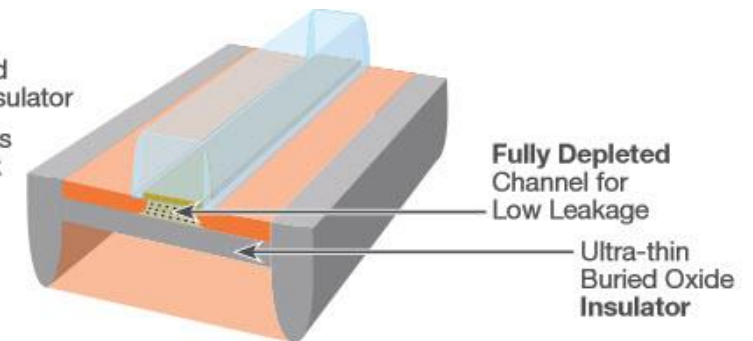
- New processes deliver power/performance/area benefit...
- ...and require unprecedented modeling / simulation accuracy
 - Device characterization/parameter extraction
 - Interconnect modeling
 - Integration into design and simulation flows
 - Integrated solutions for RF design
- IP providers require early enablement
 - Develop on early versions of the PDK
 - IP needed early to drive customer applications
 - Mobile, high performance, automotive, etc.
 - Integration to enable best-in-class flows



Source: Globalfoundries

FD-SOI

- Fully-Depleted Silicon-On-Insulator
- Planar process similar to bulk



Source: Globalfoundries

Challenges Specific To 16nm And Below

Multi-patterning

- Misalignment between masks leads to unpredictability
- Impact on parasitics is layout-dependent
- Effectively adds corners to analysis
- Creeping up to the routing layers

FinFETs

- No "one size fits all" solution
- 3D effects contribute significantly to parasitics, disrupt profile

Local interconnect

- Enables greater density, smaller standard cells
- Necessitates 3D device models

Rule-based Vs. Field Solver Approaches

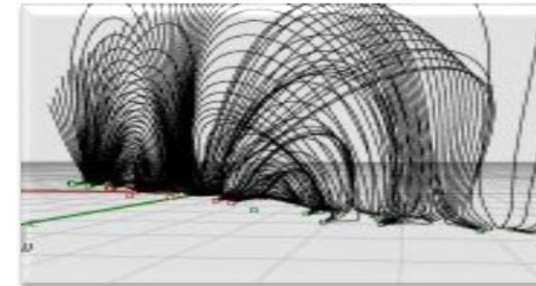
Rule-Based / Table-based



- Measures distances between polygons, looks up values from pre-characterized tables
- Fast performance

$$C = \frac{\epsilon A}{d}$$

Field Solver



- Solves Maxwell's equations
- Highest accuracy

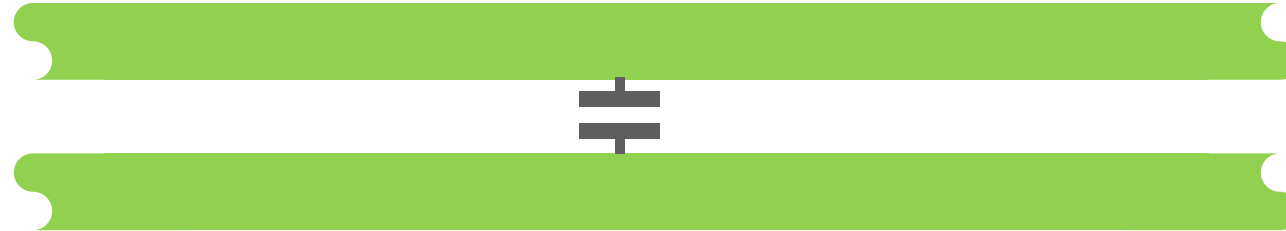
$$\vec{\nabla} \cdot \vec{E} = 0 \quad \vec{\nabla} \times \vec{E} = -\frac{\partial \vec{B}}{\partial t}$$

$$\vec{\nabla} \cdot \vec{B} = 0 \quad \vec{\nabla} \times \vec{B} = \mu\epsilon \frac{\partial \vec{E}}{\partial t}$$

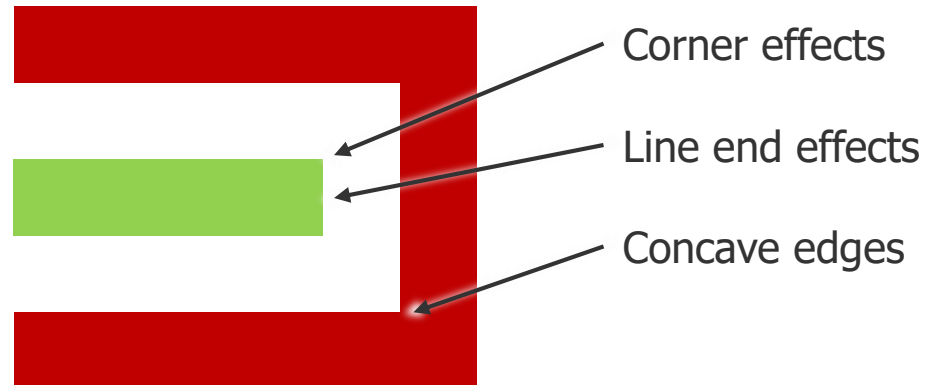
3D Line-End Effects

Long wires

$$C = \frac{\epsilon A}{d}$$



Short wires



FinFET Challenges: Modeling MOL

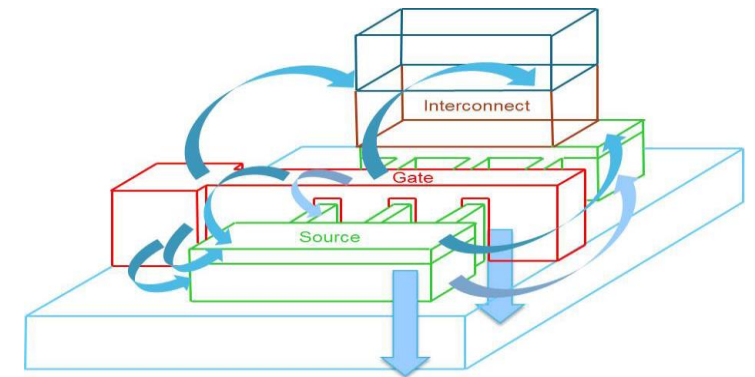
More Parasitic Effects

- Further refinement by foundries

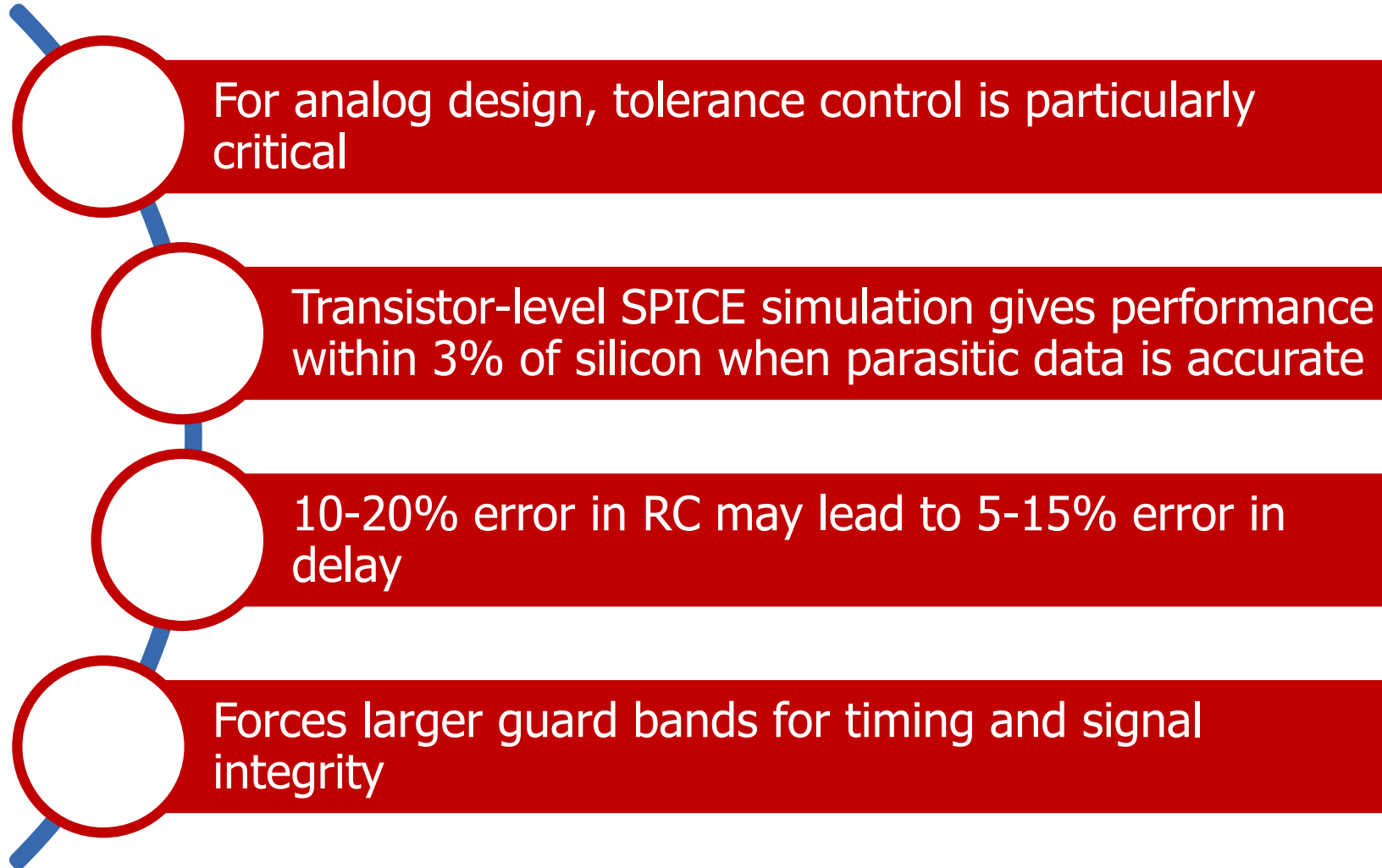
Complex Geometries

- Fin/poly/diffusion
- Local interconnect
- Contacts

Tighter Accuracy Requirements



Impact Of Extraction Errors



Calibre xACT For Full-Chip Design

A New Approach

Table-based



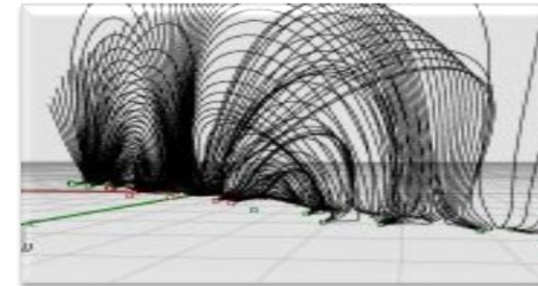
- Measures distances between polygons, looks up values from pre-characterized tables
- Fast performance

$$C = \frac{\epsilon A}{d}$$

Hybrid Approach (Calibre xACT)

Best combination of performance and accuracy for advanced nanometer processes

Field Solver



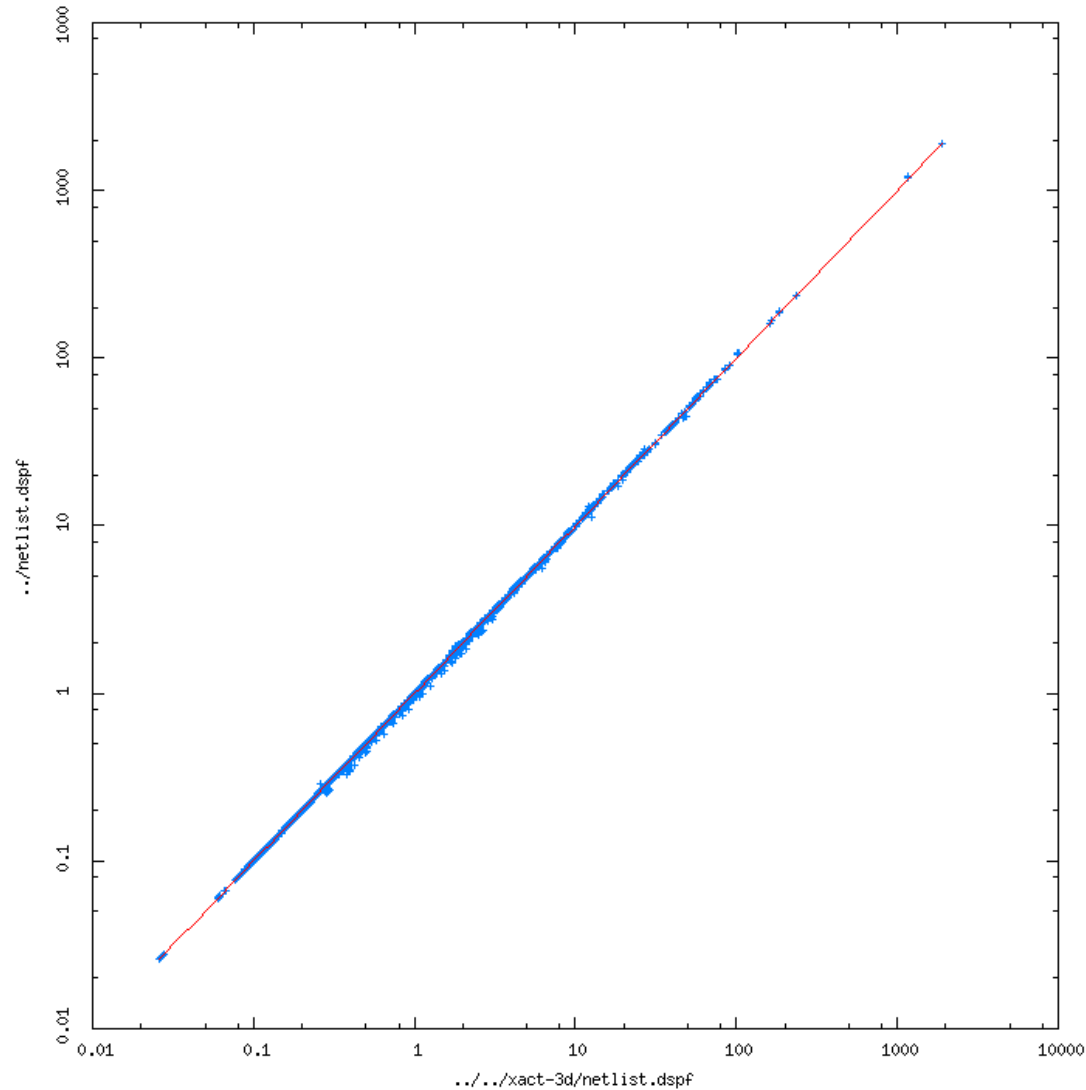
- Solves Maxwell's equations
- Highest accuracy

$$\vec{\nabla} \cdot \vec{E} = \frac{\rho}{\epsilon} \quad \vec{\nabla} \times \vec{E} = -\frac{\partial \vec{B}}{\partial t}$$

$$\vec{\nabla} \cdot \vec{B} = 0 \quad \vec{\nabla} \times \vec{B} = \mu\epsilon \frac{\partial \vec{E}}{\partial t}$$

Calibre xACT Accuracy

N16 customer testcase



Calibre xACT vs. Calibre xACT 3D field solver

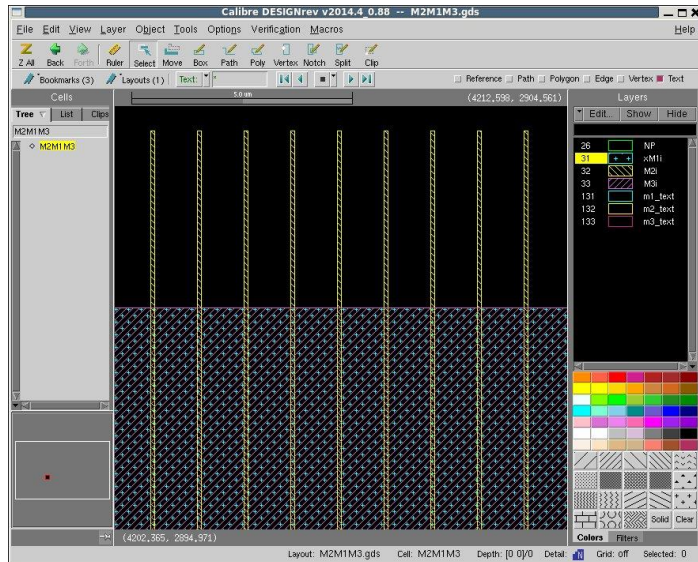
Min	-13.1
Max	11.3
Mean	-0.1
Std dev	0.6

Filtered 5e-16

Calibre xACT Accuracy

Foundry test pattern vs. foundry golden

- All tools meet foundry qualification requirements
- Field solver has tighter standard deviation



Metric	Calibre xACT	Calibre xACT 3D field solver
Min	-5.5	-3.9
Max	3.2	2.1
Mean	0.1	-0.2
Std dev	1.5	1.1

Calibre xACT Product Portfolio

- Calibre xACT – hybrid extraction engine – performance + accuracy for leading-edge, full-chip custom/analog/RF and digital design
- Calibre xACT 3D Field Solver – no-compromise, high performance field solver accuracy for memory and cell design
 - Order of magnitude faster than traditional FS
 - Repeatable, deterministic results (as opposed to statistical tools which have inherent error)
 - Capacity for multi-million transistor blocks
 - Common Calibre rule decks and use model
- Calibre xL – loop and partial inductance extraction for RF and high-performance design
 - Parasitic inductance associated with signal/return-path “loops”
 - Full chip inductance extraction of on-chip signal interconnects
 - Application in Analog and Digital design, Clock network, Transmission lines...
 - “PEEC” - selected critical nets extraction
 - Self partial inductance L and mutual inductance M for extracted for each conductor segment.
 - Application In RF/Analog critical signals, Differential Pairs, Small P/G nets...

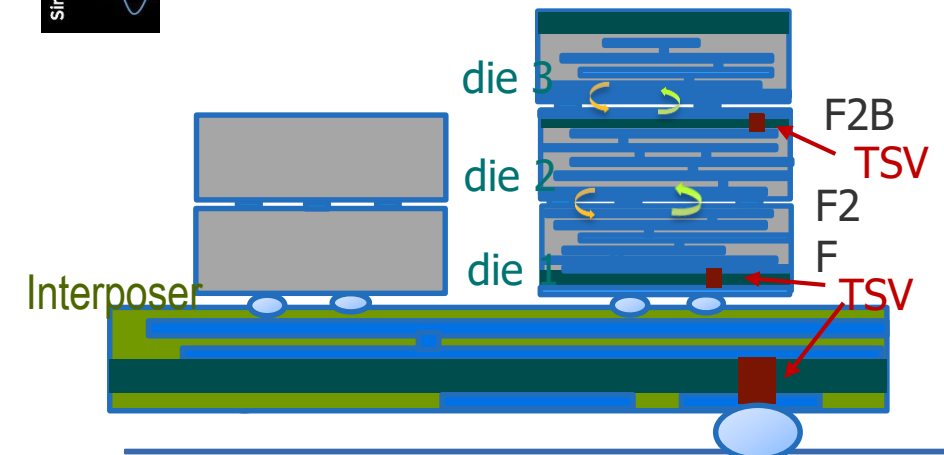
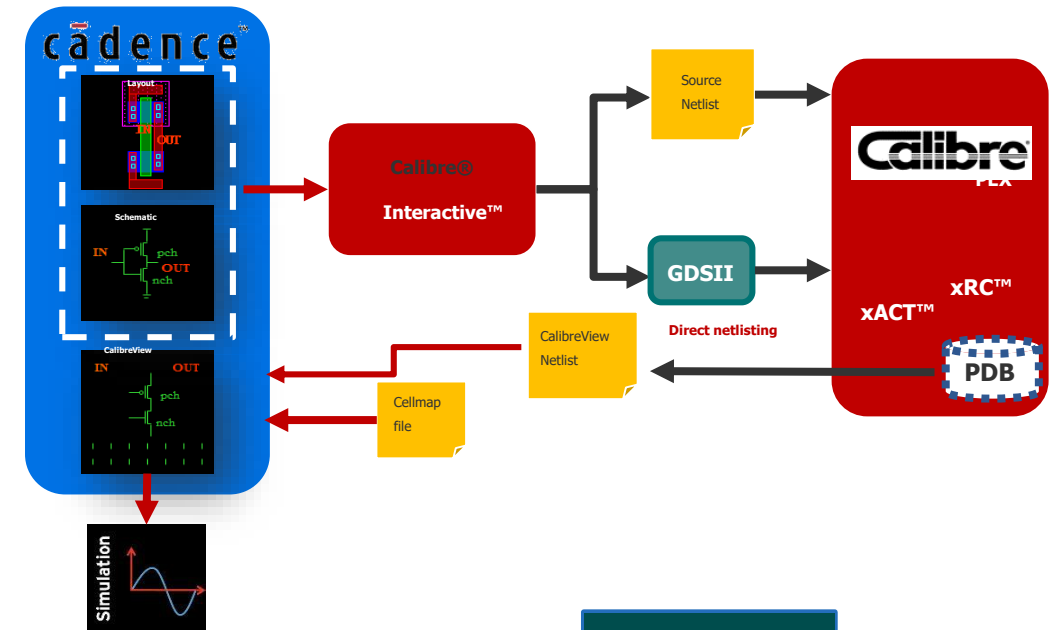
Calibre xACT Flows And Applications

■ Calibreview

- Designers never have to leave the implementation cockpit
- A Calibreview passes Calibre nmLVS and Calibre extracted parasitics to Cadence Virtuoso design environment
- Contains the connectivity and intentional devices the Calibre LVS tool extracts, as well as parasitic devices extracted by Calibre PEX

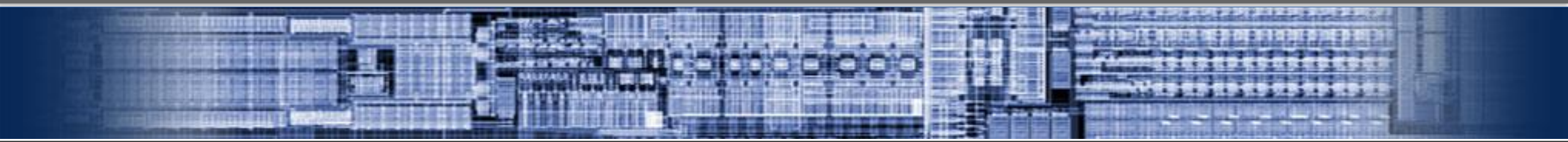
■ 3DIC extraction solutions for configurations including

- Fan Out Wafer Level Processing (FOWLP)
- Wafer on Wafer stacking (F2F and F2B)



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Developing Leading IP

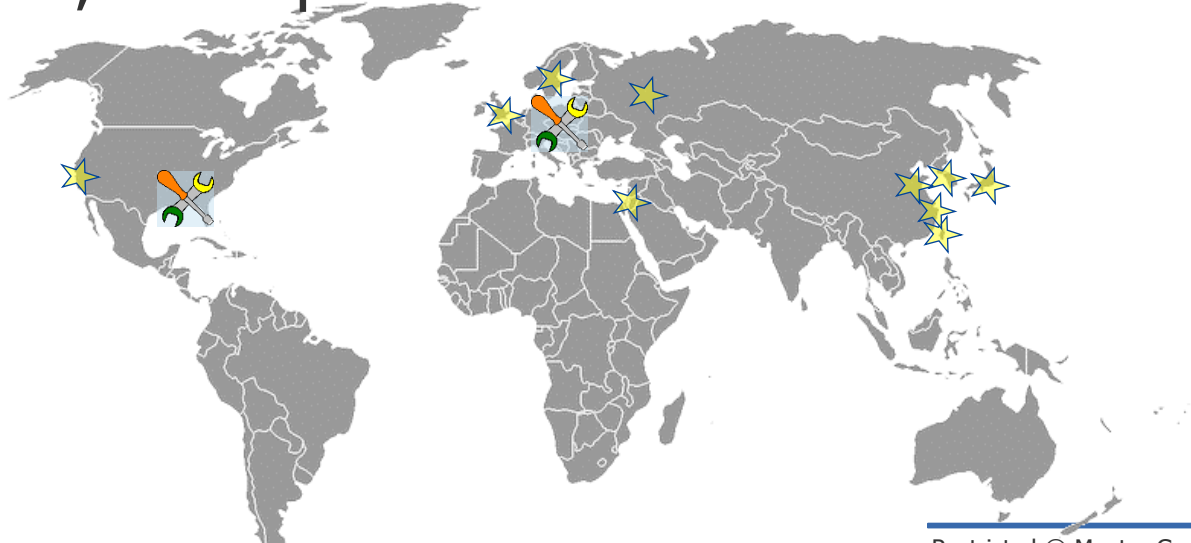
Agenda: Developing Leading IP

Collaboration between Silicon Creations and Mentor

- Introduction to Silicon Creations
- Challenges of developing PLLs & SerDes in advanced FinFET processes
- Using Calibre xACT and AFS for 5nm FinFET IP Development
- Silicon – Simulation correlations
- Summary/Q&A

Silicon Creations Overview

- IP provider of PLLs, Oscillators and High-speed Interfaces
- Founded 2006 – self-funded, profitable and growing
- Design offices in Atlanta and Krakow, Poland
- High quality development, award winning support
- >160 customers (>60 in China)
- Over 10 foundries, mass production from 7nm to >180nm, 5nm coming



Awards for quality & support

TSMC

- 2017: Audience choice paper, USA OIP
- 2017: "Mixed-Signal IP Partner of the year"
- 2014: "Best Emerging IP vendor"

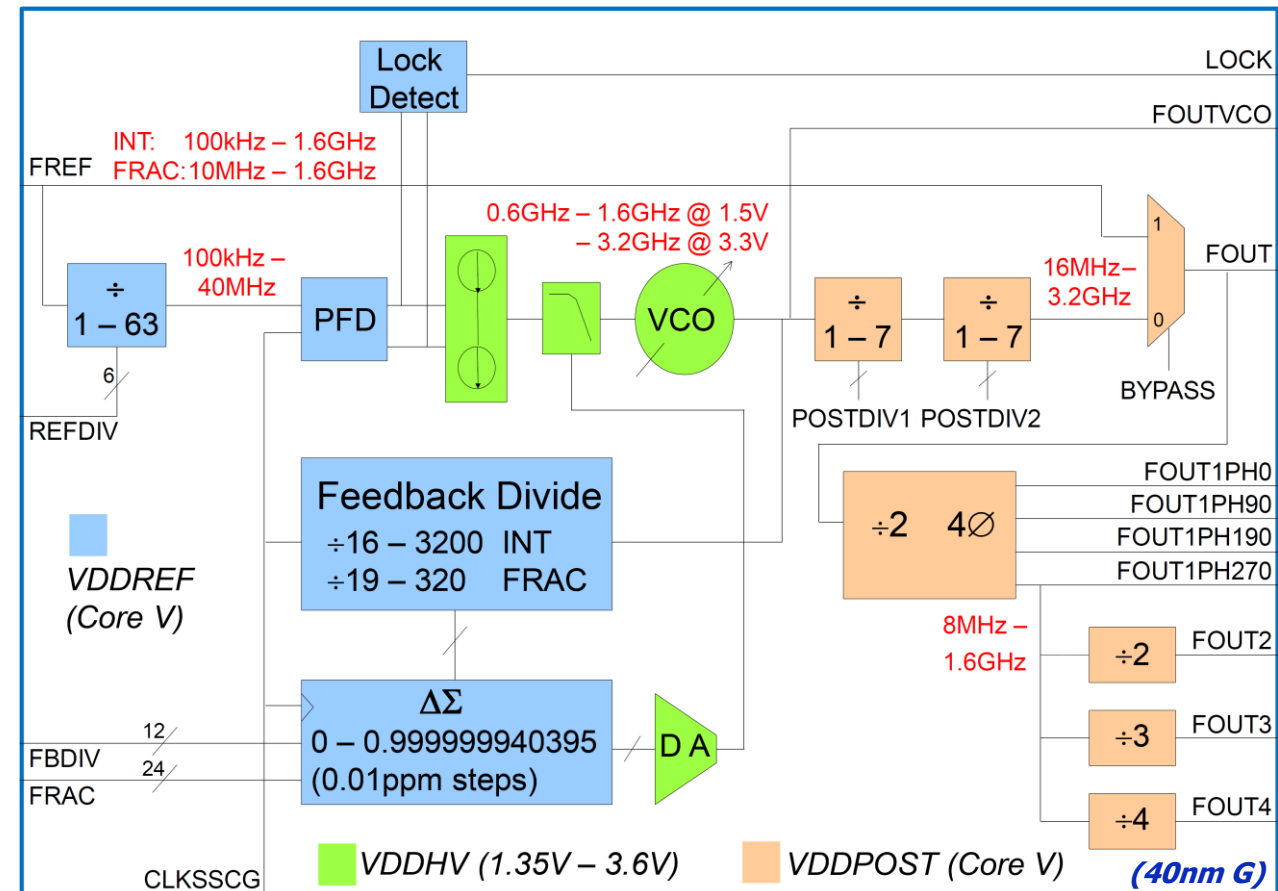
SMIC

- 2017 (no awards to anyone)
- 2015 & 2016: Best support
- 2014: Production volume growth
- 2013: Best Analog IP



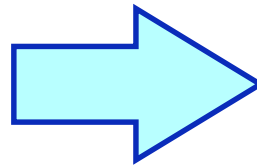
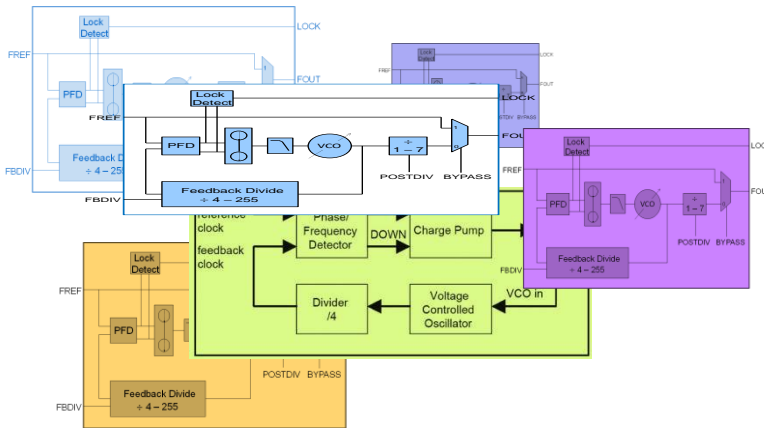
Fractional Ring PLL

- “One-Size-Fits-All” Synthesizer: flexibility reduces risk
 - Any crystal; <0.01ppm frequency step
- Programmable Power – Jitter Optimization
 - < 1mW
 - Long Term Jitter < 5ps RMS
- Production from 7nm – 180nm, 5nm in development
 - >150 chips, > 1M wafers in 28nm
 - > 40 chips, > 800k wafers in 16nm
- Derivative PLLs for
 - Core voltage only
 - Integer-only
 - Low area
 - Ultra-low jitter
 - Ultra-low power



Why our Fractional PLL?

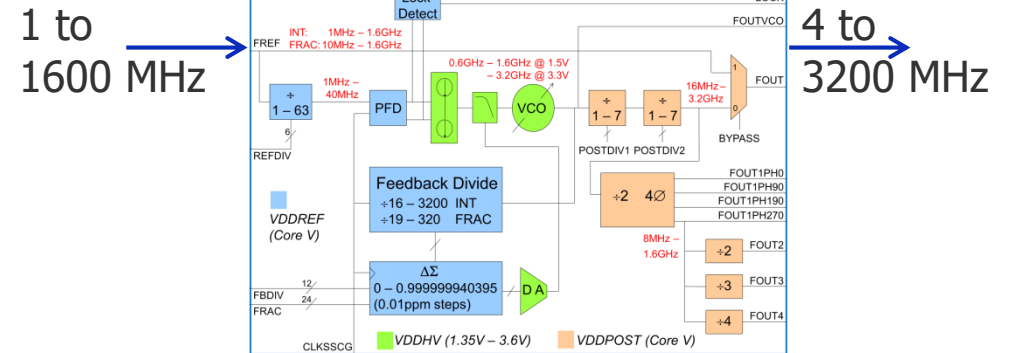
Competitor PLLs



Risky & expensive

- Built new each time
- Narrow input/output ranges
... new silicon to change
- Buy a new IP for every clock

Silicon Creations

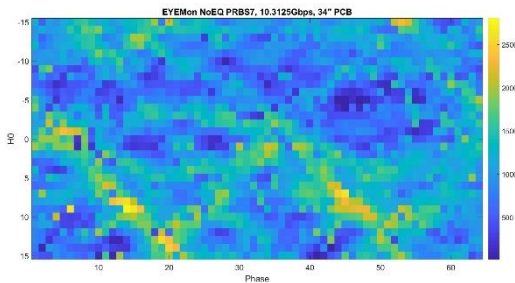


Lower risk & lower cost

- Predictable, measured
- Wide range, programmable
power-performance tradeoffs
- One PLL, many applications – save \$, ¥, €
- Best support

Multi-Protocol SerDes PMA

- 0.25 – 12.7Gbps SerDes PMA (28nm LP, 40 LP, 12FFC soon)
- Low Power (mW/Gpbs/lane): SR ~4.5mW, LR ~8.6mW
- Jitter cleaner Tx Ring PLL → Low Area

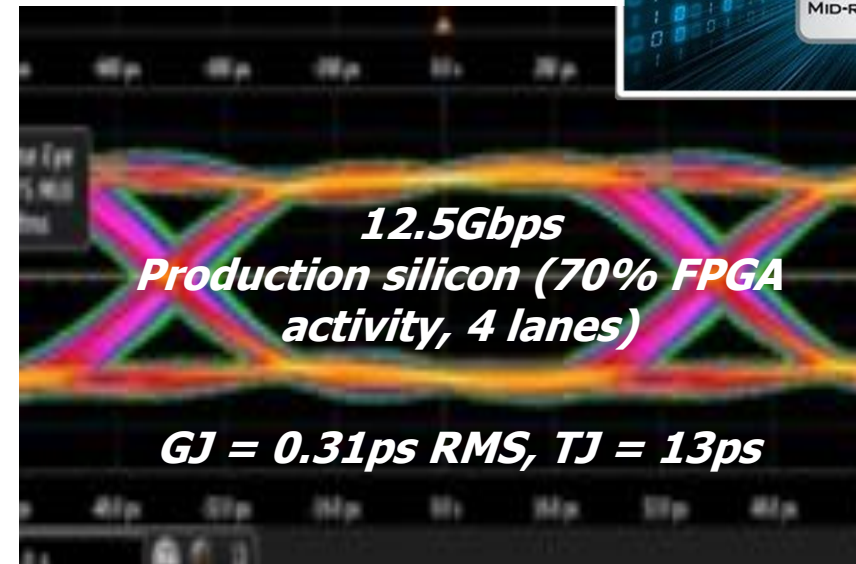
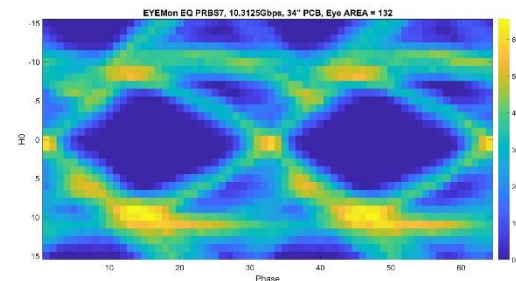


(10.3Gbps,
25dB channel loss)



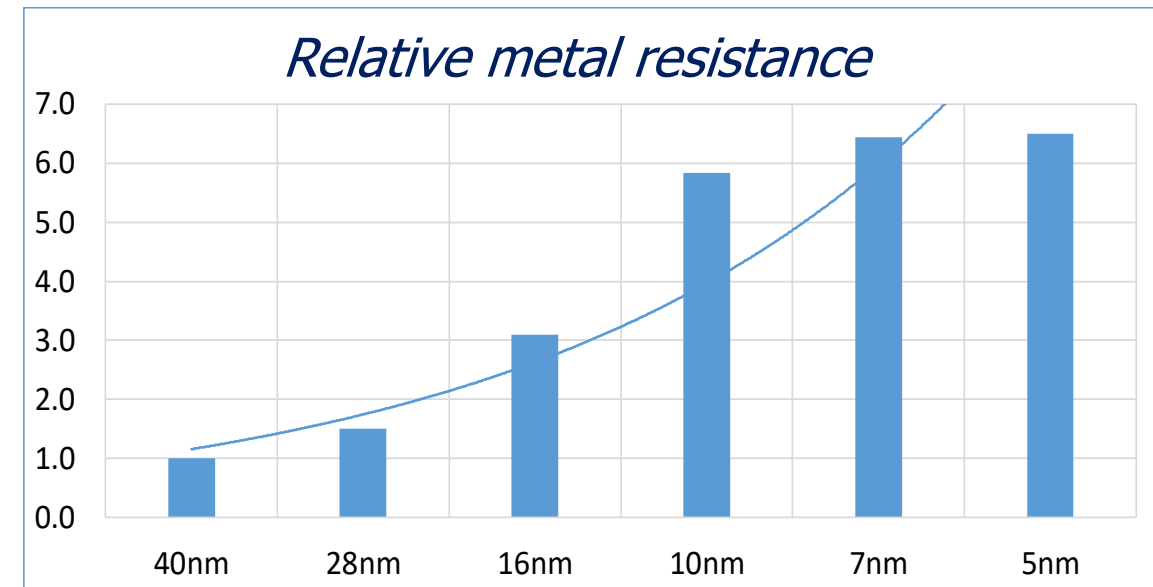
5-tap DFE + CTLE +
Eye monitor +
Adaptive Eq.

→ **>30 protocols**



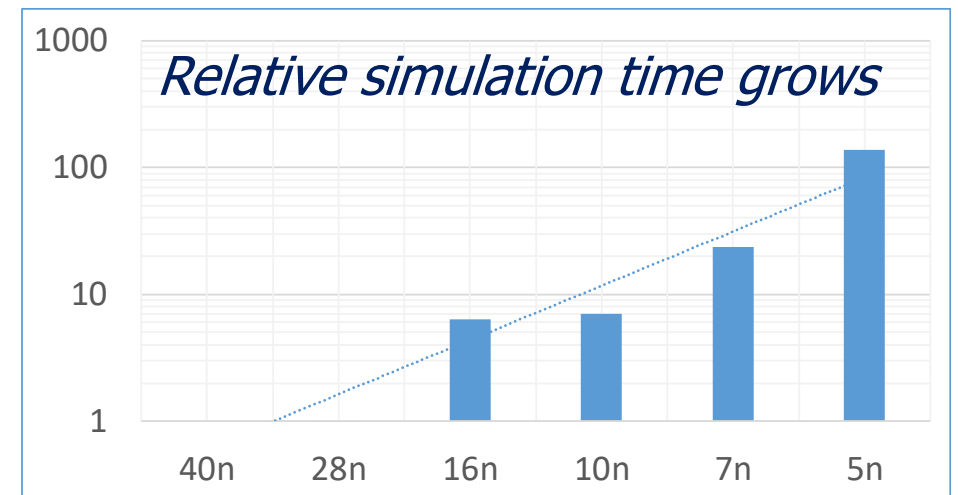
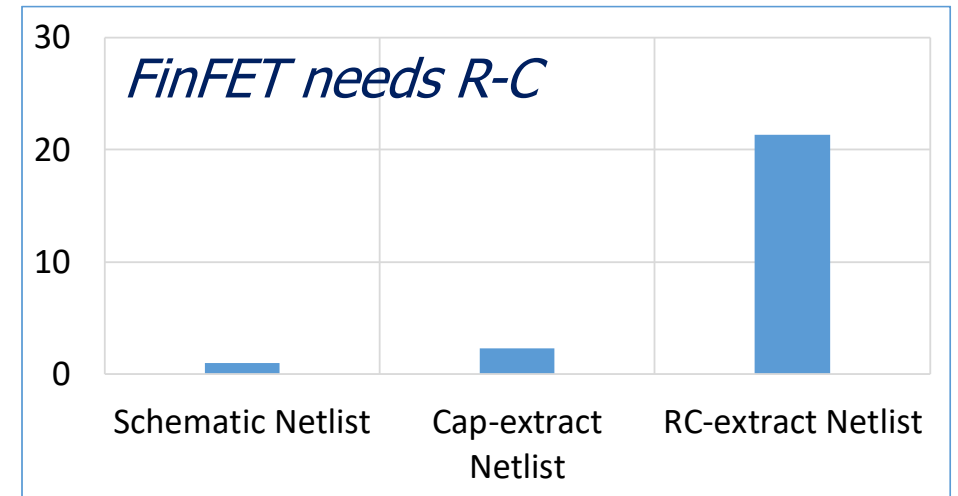
Wire resistance challenge

- Interconnect resistance is climbing quickly!
- Extraction and post extract simulations are becoming more important
- From 40nm to 5nm/7nm, wire resistance (Ω/sq) has risen $\sim 6.5x$
- Designs are increasingly difficult to verify due to the need for simulation of distributed RC parasitics



5nm Simulation Time

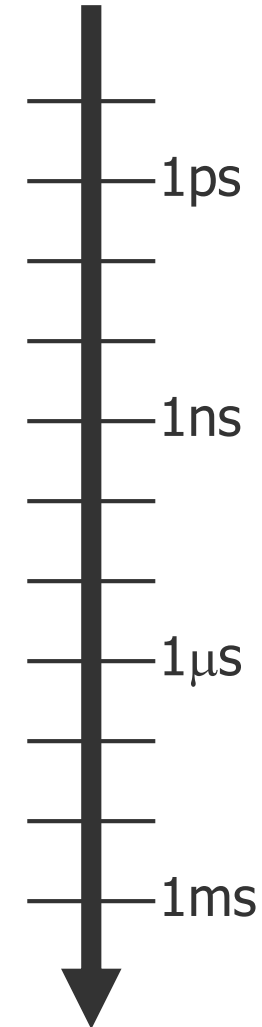
- Schematic sims are out, distributed C-C and R-C extracted simulations are essential
 - We use Calibre Xact to generate accurate netlists
- Models are becoming more complex
 - Higher development costs:
 - Longer development cycles
 - Need parallel simulation and more CPU's
 - Need more EDA licenses



Simulation time scale

Makes things worse for PLLs & SerDes

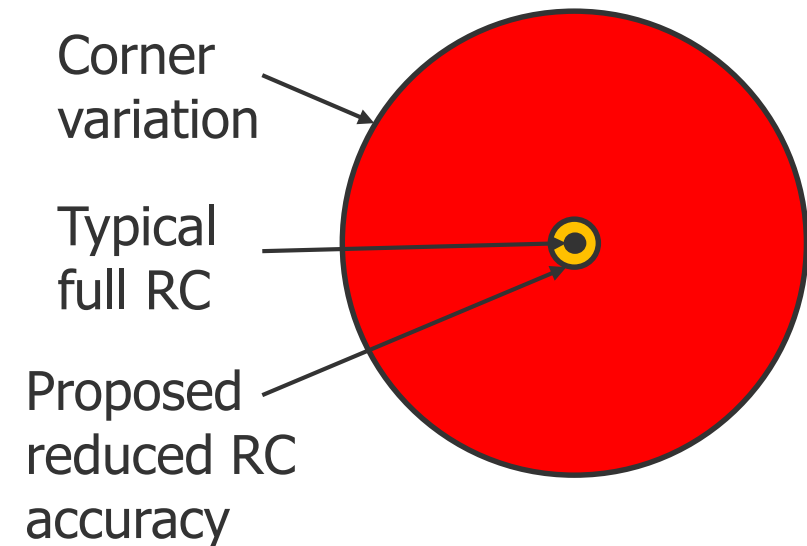
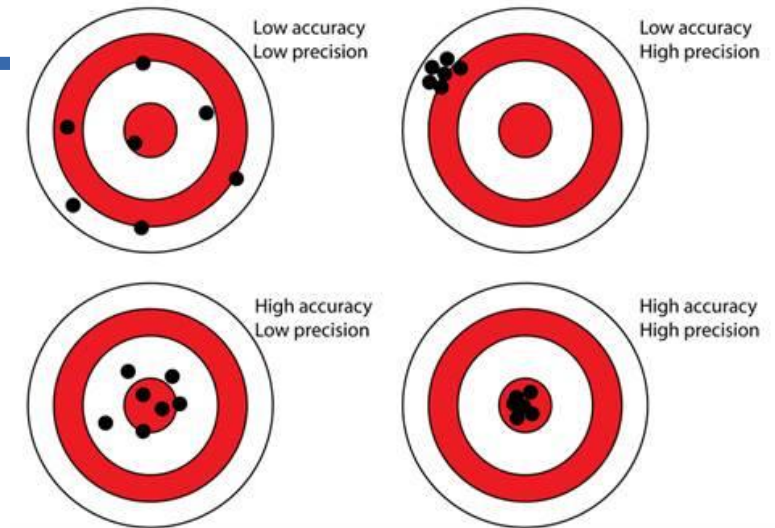
- Jitter requirements $\sim 0.1\text{ps}$ ----->
- Bit rates / clock cycle time $\sim 100\text{ps}$ ----->
- AC coupling time constant $\sim 1\mu\text{s}$ ----->
- PLL lock time $\sim 50\mu\text{s}$ ----->
- Link behavior $\sim 1\text{ms}$ ----->



10 orders of magnitude!

RC Reduction and Accuracy

- RC reduction is one way to decrease simulation time (and cost!)
- Goal: reduce simulation time (lower cost), but preserve reasonable accuracy
 - Corner spread is typically $\sim 40\%$
 - Some precision can be lost without much effect on margin



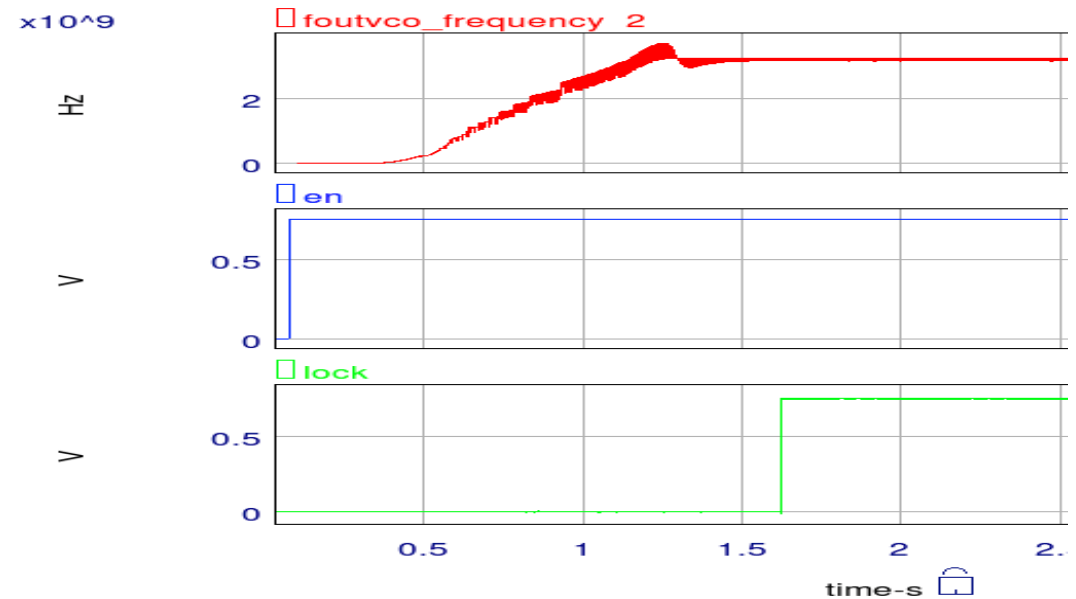
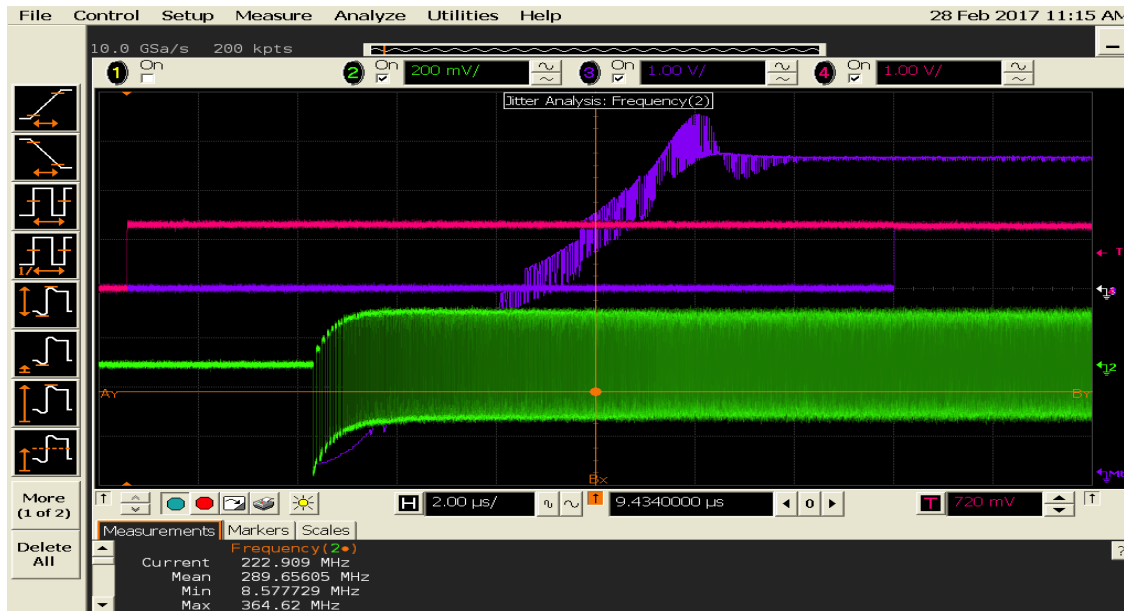
RC Reduction Example – 28nm VCO

- Example:
 - compare full RC & reduced RC, CC & reduced CC
 - Look for accuracy, simulation time (cost)
- Full RC netlist used as the “gold standard”
- CC netlist runs in 1/10th the time, but at a 7% frequency error
- Highlighted strategy
 - Join R’s < 1 Ohm, merge C’s < 0.1fF
 - Total cost, in units of [token*seconds], is reduced 6x
 - Frequency error only ~0.1%
- Strategy and merge thresholds depend on block, process
 - significant time (cost) savings possible!

Simulation	Relative Frequency Error [%]	Relative Time [%]	AFS Tokens	Relative Cost [%]
RCC - gold stanard	0.000	100.0	2	100.0
RCC w/ 30GHz Tau reduction	0.024	91.3	2	91.3
RCC w/ 10GHz Tau reduction	0.024	90.9	2	90.9
RCC - join R < 0.1 Ohm, join C < 0.01 fF	0.004	52.2	2	52.2
RCC - join R < 1 Ohm, join C < 0.1 fF	0.125	34.8	1	17.4
CC only	6.909	10.4	1	5.2
CC only, join C < CABS 10%	5.554	9.4	1	4.7

7nm Area Optimized PLL Locking Simulation vs. Measurement

- Lowest area PLL for digital clocking – 0.009mm²
- Total power under 200μW
- Accurate netlist provides an excellent correlation between AFS transient simulation of frequency vs. time and silicon measurements



7nm IoT PLL Current Consumption

Accurate parasitics → first time right design

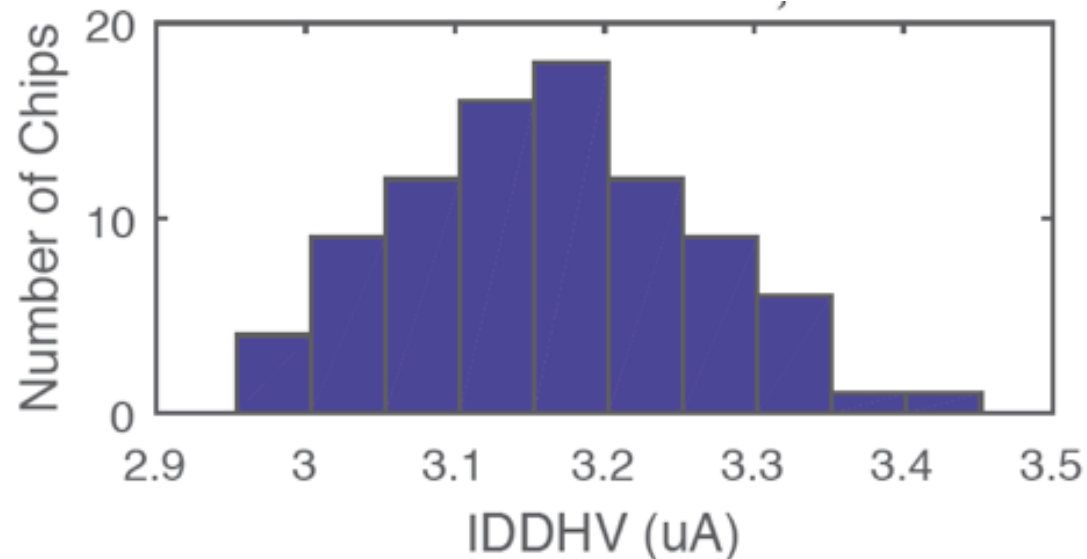
■ Simulation

- Mean=3.02uA
- Stddev=1.5%

■ Measurement

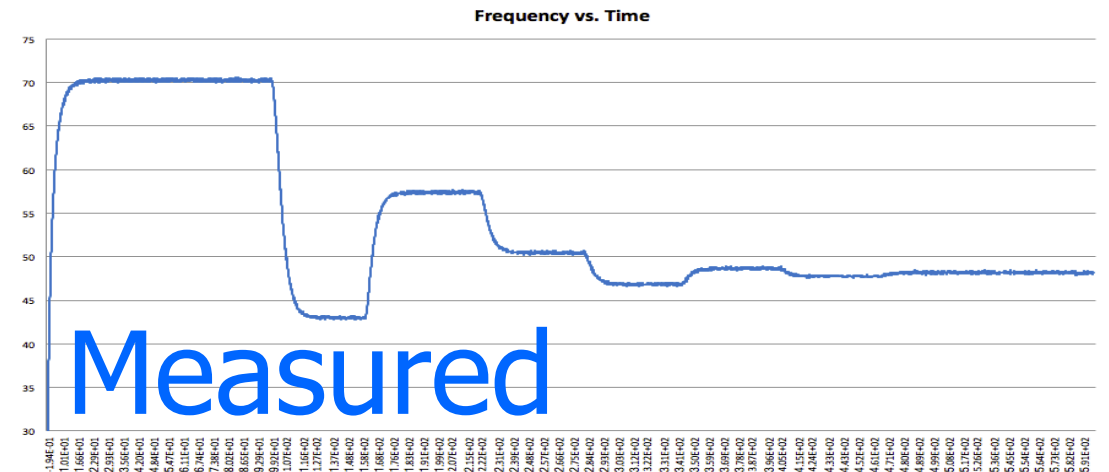
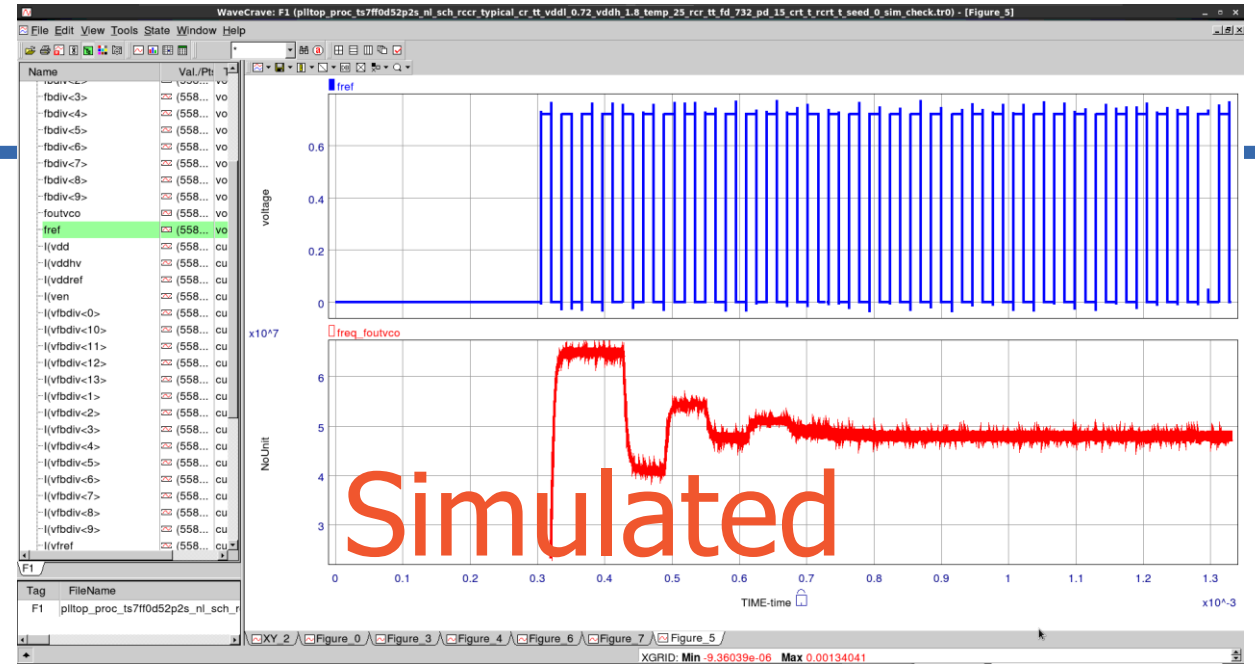
- Mean=3.15uA
- Stddev=1.6%

Measured Supply Current



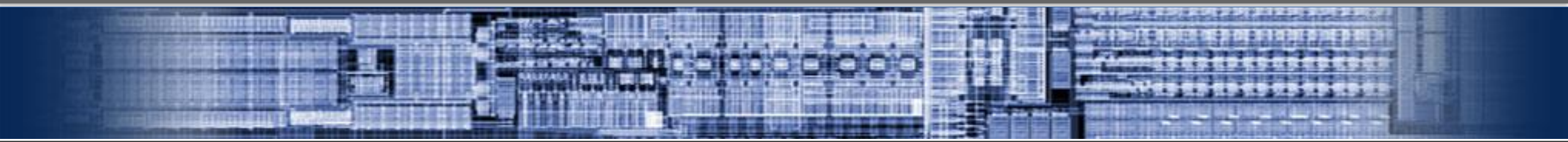
IoT PLL Fast Locking

- AFS transient simulations accurately predict locking behavior (VCO frequency vs. time)
- 32kHz locking simulations must run for $>1\text{ms}$, so we need not only a fast locking PLL, but also
 - A fast simulator
 - Accurate netlist from Xact (carefully reduced)



Silicon Creations Summary

- Key challenges for FinFET PLLs & SerDes
 - Necessarily long simulations due to tiny time steps and need to simulate a long time for loops to settle
 - High metal resistance requires distributed RC-extraction and netlist reduction if we want simulation results before the silicon comes back
- Solution
 - Really accurate extraction from Calibre Xact provides this
 - A powerful and fast simulator – Mentor AFS
- The reward – for us and our customers
 - 7nm low jitter PLLs and ultra-low power PLLs that go to production on first silicon



Thank you!